

13281 U.S. PTO
031504

Steven M. Rabin
Robert H. Berdo, Jr.
Phillip G. Avruch
Allen Wood
Qixia Zhang, Pat. Agent (China)

RABIN & BERDO, P.C.
*Specializing in Patent, Trademark
And Copyright Law*

Suite 500, 1101 14th Street, N.W.
Washington, D.C. 20005
Tel.: (202) 371-8976 Fax: (202) 408-0924
E-Mail: firm@rabinchamp.com

March 15, 2004

In Affiliation with
Weiss, Moy & Harris, PC
having offices in Arizona and Nevada,
and in Washington, DC with
Rabin & Berdo, PC

15364 U.S. PTO
10/800013
031504

Mail Stop: Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attorney Reference: FEC 121

Re: New Patent Application of: Hiroshi TOBISAKA, Tatsuhiko FUJIHIRA
Shin KIUCHI, Yoshiaki MINOYA
Takeshi ICHIMURA, Naoki YAEZAWA
Ryu SAITOU, Shouichi FURUHATA
and Yuichi HARADA

Title: SEMICONDUCTOR DEVICE HAVING TRANSISTOR WITH HIGH
ELECTROSTATIC DISCHARGE CAPABILITY AND HIGH NOISE
CAPABILITY

Sir:

Please find attached hereto an application for patent which includes:


- ☒ Specification, Claims and Abstract (18 pages)
- ☒ 2 Sheets of Formal Drawings (Fig. 1 through Fig. 4)
- ☐ Information Disclosure Statement,
Form PTO-1449, copies of references
- ☒ Claim for priority
- ☐ Fee (see formula below)

The right of priority is claimed under 35 USC §119 of Japanese Application No.
2003-107830, filed April 11, 2003(document to be submitted later).

Respectfully submitted,

March 15, 2004
Date

SMR:tl


Steven M. Rabin (Reg. No. 29,102)
(Customer No. 23995)